

LISTING OF THE CLAIMS

1. (Previously Presented): An in-plane switching mode LCD device comprising:
first and second substrates;
data and gate lines on the first substrate to define a plurality of pixel regions;
at least one data electrode on the first substrate;
at least one common electrode on the first substrate;
a transparent conductive film in a layer over the common electrode, the transparent conductive film electrically connected with the common electrode; and
a liquid crystal layer between the first and second substrates.
2. (Original): The device of claim 1, wherein the transparent conductive film includes indium tin oxide (ITO).
3. (Original): The device of claim 1, further comprising a gate insulating film on the common electrode.
4. (Original): The device of claim 1, further comprising a passivation film on the common electrode.
5. (Original): The device of claim 4, wherein the common electrode is electrically connected with the transparent conductive film through a contact hole in the passivation film.
6. (Original): The device of claim 1, wherein the common electrode is electrically connected with the transparent conductive film through a laser welding.
7. (Original): The device of claim 1, wherein the liquid crystal layer includes a cyano (CN) based liquid crystal.
8. (Original): The device of claim 1, wherein the liquid crystal layer includes a fluorine (F) based liquid crystal.

9. (Original): The device of claim 1, wherein the transparent conductive film is formed outermost to the common electrode.

10. (Original): The device of claim 1, wherein the transparent conductive film extends toward the data electrode.

11. (Previously Presented): A method for manufacturing an in-plane switching mode LCD device comprising:

- providing first and second substrates;
- forming a plurality of gate lines and common electrodes on the first substrate;
- forming a gate insulating film on the common electrodes;
- forming a plurality of data lines and data electrodes on the gate insulating film;
- forming a transparent conductive film in a layer over the common electrodes, the transparent conductive film electrically connected with the common electrodes; and
- forming a liquid crystal layer between the first and second substrates.

12. (Original): The method of claim 11, wherein the common electrode is selected from the group of consisting of Al, Cr, Ti and Al alloy.

13. (Original): The method of claim 11, further comprising the step of forming a passivation film on the data electrodes.

14. (Original): The method of claim 11, wherein the common electrode is electrically connected with the transparent conductive film through a contact hole of the passivation film.

15. (Original): The method of claim 11, further comprising the step of electrically connecting the common electrodes with the transparent conductive film.

16. (Original): The method of claim 15, wherein the common electrode is electrically connected with the transparent conductive film through a laser welding.

17. (Original): The method of claim 11, wherein the transparent conductive film includes indium tin oxide (ITO).

18. (Original): The method of claim 11, wherein the liquid crystal layer includes a cyano (CN) based liquid crystal.

19. (Original): The method of claim 11, wherein the liquid crystal layer includes a fluorine (F) based liquid crystal.

20. (Original): The method of claim 11, wherein the transparent conductive film is formed outmost to the common electrodes.

21. (Original): The method of claim 11, wherein the transparent conductive film extends toward at least one of the data electrodes.